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ORIQ

Silicon Bipolar MMIC Frequency Converter July, 1986

MSF-8885

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#### **Features**

- Up or Down Frequency Conversion with up to 20 dB Conversion Gain
- RF Input From 0.5 to 10 GHz
- Low Phase Noise Self-Oscillating LO From 0.5 to 8 GHz Using External Tank Circuit
- Downconverted IF Output from dc to 2 GHz
- Uniform Performance
- Low Power Consumption per Function
- Low Cost per Function
- Low-Cost 85 mil Plastic Microstrip Package

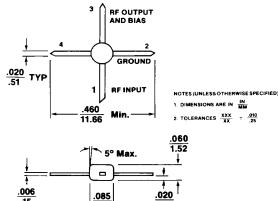
#### Markets

- GPS Navigation and INMARSAT Receivers
- Satellite MATV and TVRO Block Converters
- MDS Multipoint Distribution System TV
- 2nd IF for Police Radar Detectors
- Mobile and Cellular Radio Receivers
- CATV Converters
- Military Manpack and Mobile Receivers
- Communications and Radar Systems
- Low-Cost Self-Detecting Doppler Radar

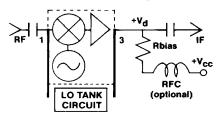
# **Description**

The MSF-8885 is a member of Avantek's Monolithic Silicon Frequency (MSF) converter MMIC building block family. It is optimized to simultaneously function as a self-oscillating LO and two-port active mixer with up or down conversion gain. It is ideally suited for very low cost or size constrained applications where adequate conversion gain flatness, LO-RF and LO-IF isolation or spurious signal rejection can be achieved using simple external filters.

## Avantek 85 Plastic Package



### **Functional Block Diagram**



The MSF series is fabricated using a 10 GHz Ft silicon bipolar MMIC process that features sub-micrometer nitride self-alignment and ion-implantation to achieve excellent unit-unit uniformity. Biasing requires a fixed single polarity supply with an external current stabilizing resistor.

## Electrical Specifications: $T_a = 25^{\circ}$ C, $I_d = 35$ mA, $Z_o = 50$ ohms, -20 dBm RF Input at 4.2 GHz and LO at 5.15 GHz

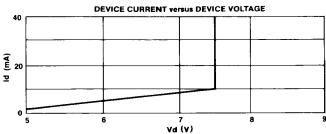
Symbol	Parameter	Freq. (GHz)	Units	Min.	Тур.	Max.
G <sub>C</sub>	Conversion Gain to 0.95 GHz IF	4.20	dB	7	9	
P <sub>1dB</sub>	Output Power at 1dB Compression	0.95	dBm		9	
IP3	3rd-order Output Intercept Point	0.95	dBm		16	
S	IF Band Spurious Signal Level (4RF-3LO)	1.35	dBc		<70	
NF	Single-Side-Band Noise Figure	4.20	dB		12	
VSWR	Input VSWR	.5-6			2.5:1	
VSWR	Output VSWR	.5-2			2.5:1	
V <sub>d</sub>	Device Voltage		Vd		7.5	
V <sub>dtc</sub>	Device Voltage Temp. Coefficient		mV/C		-11	
I <sub>d</sub>	Normal Operating Current Range	_	mA	20	35	40

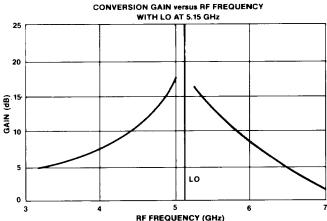
PATENT PENDING

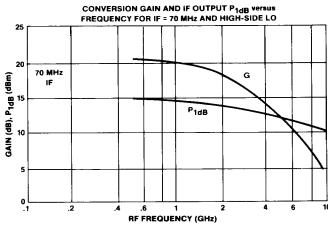
## **ABSOLUTE MAXIMUM RATINGS**

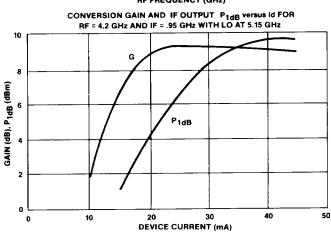
Device Current	
RF Input Power	
Junction Temperature	
Storage Temperature 150	)° C
Thermal Resistance Θ <sub>jc</sub> <150°C	C/W

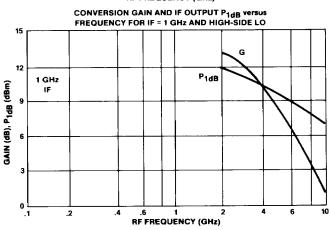
# Typical Performance, T<sub>a</sub> = 25° C, I<sub>d</sub> = 35 mA

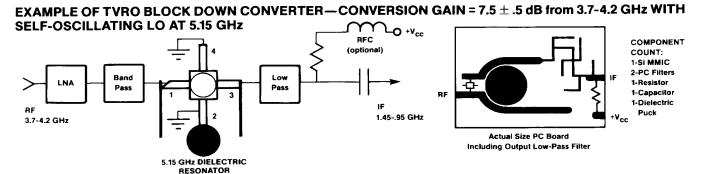














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